

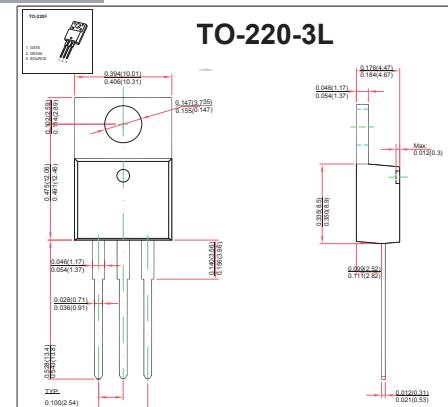
TO-220-3L Plastic-Encapsulate MOSFETS

FEATURE

- N-Channel Power MOSFET
- High Current Rating
- Lower RDS(on)
- Lower Capacitance
- Lower Total Gate Charge
- Tighter VSD Specifications
- Avalanche Energy Specified

MECHANICAL DATA

- Case style: TO-220-3L molded plastic
- Mounting position: any



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	600	V
Gate-Source Voltage	V _{GS}	±30	
Continuous Drain Current	I _D	8	A
Pulsed Drain Current	I _{DM}	32	
Single Pulsed Avalanche Energy (note1)	E _{AS}	250	mJ
Power Dissipation	P _D	2	W
Thermal Resistance from Junction to Ambient	R _{θJA}	62.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 ~+150	
Maximum lead temperature for soldering purposes , Duration 5 seconds	T _L	260	°C

MOSFET ELECTRICAL CHARACTERISTICS T_A=25°C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	600			V
Drain-source diode forward voltage(note2)	V _{SD}	V _{GS} = 0V, I _S = 7A			1.4	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 600V, V _{GS} = 0V			1	μA
Gate-body leakage current (note2)	I _{GSS}	V _{DS} = 0V, V _{GS} = ±30V			±100	nA
On characteristics (note2)						
Gate-threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Static drain-source on-resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 4A			1.3	Ω
Dynamic characteristics (note 3)						
Input capacitance	C _{iss}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz			1280	pF
Output capacitance	C _{oss}				120	
Reverse transfer capacitance	C _{rss}				11	
Switching characteristics (note 3)						
Turn-on delay time (note3)	t _{d(on)}	V _{DD} = 300V, V _{GS} = 10V, R _G = 25Ω, I _D = 7A			80	ns
Turn-on rise time (note3)	t _r				165	
Turn-off delay time (note3)	t _{d(off)}				160	
Turn-off fall time (note3)	t _f				120	

Notes :

- I_L=8A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C.
- Pulse Test : Pulse width≤300μs, duty cycle ≤2%.
- These parameters have no way to verify.